Oxford ICP Etcher
Chromium Etch Recipe

Etch Rate: ~ 25 nm/min

Steps

1. Temperature Stabilization
   a. Run for 2 minutes at 25 °C.

2. Cl₂ & O₂ Plasma
   a. Run for 4 minutes and 30 seconds at 25 °C and 10 mTorr.
   b. Flow of
      i. Cl₂ – 26 sccm
      ii. O₂ – 4 sccm
      iii. He backing – 10 sccm
   c. Power
      i. RF Generator – 20 W
      ii. ICP Generator – 400 W

3. Pump to 1e-5
   a. Pump down to pressure of 1 x 10⁻⁵ Pa.

4. Ar Purge
   a. Run for 2 minutes at 25 °C and 20 mTorr.
   b. Flow of
      i. Ar – 100 sccm
      ii. He backing – 10 sccm

5. Pump to 5e-6
   a. Pump down to pressure of 5 x 10⁻⁶ Pa.

6. Ar Purge
   a. Run for 2 minutes at °C and 20 mTorr.
   b. Flow of
      i. Ar – 100 sccm
      ii. He backing – 10 sccm

7. Pump to 5e-6
   a. Pump down to pressure of 5 x 10⁻⁶ Pa.